

Abstract

A method for forming DRAM cell bit-line contact is provided. First a dielectric layer is formed on a substrate on which a plurality of control gates has already been formed, and then a patterned photoresist defining a first aperture is formed thereon. Afterwards, through the patterned photoresist the dielectric layer is etched away to expose the substrate there beneath to form the bit-line contact window. Thereafter the bit-line contact windows are filled with a conductive material to form the bit-line contact. Finally, a conductor layer is formed on a previously formed isolation layer, which has a second aperture and the partially exposed bit-line contact, to fill the second aperture.